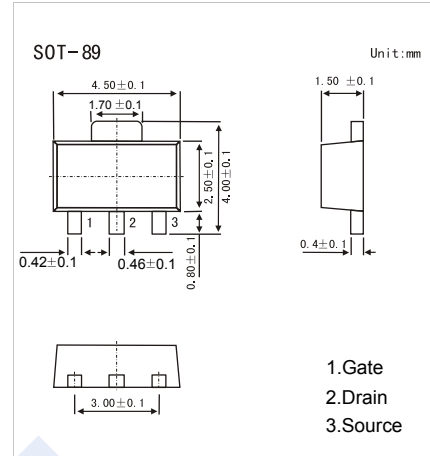


P-Channel MOSFET

2SJ288

■ Features

- V_{DS} (V) = -60V
- I_D = -0.5 A
- $R_{DS(ON)} < 3 \Omega$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 4 \Omega$ ($V_{GS} = -4V$)



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V_{DS}	-60	V	
Gate-Source Voltage	V_{GS}	± 15		
Continuous Drain Current	I_D	-0.5	A	
Pulsed Drain Current (Note.1)	I_{DM}	-2		
Power Dissipation	P_D	$T_c = 25^\circ\text{C}$	3.5	W
			1.3	
Junction Temperature	T_J	150	$^\circ\text{C}$	
Junction Storage Temperature Range	T_{stg}	-55 to 150		

Note.1: $PW \leq 10 \mu\text{s}$, duty cycle $\leq 1\%$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

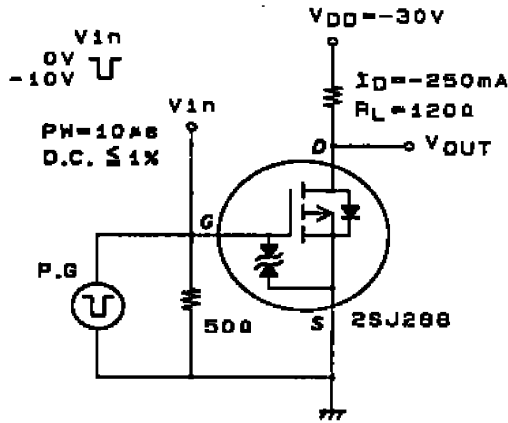
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = -1\text{mA}$, $V_{GS} = 0V$	-60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60V$, $V_{GS} = 0V$			-100	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0V$, $V_{GS} = \pm 12V$			± 10	μA
Gate to Source Cutoff Voltage	$V_{GS(off)}$	$V_{GS} = -10V$, $I_D = -1\text{mA}$	-1		-2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V$, $I_D = -250\text{mA}$			3	Ω
		$V_{GS} = -4V$, $I_D = -250\text{mA}$			4	
Forward Transconductance	g_{FS}	$V_{DS} = -10V$, $I_D = -250\text{mA}$	240	400		mS
Input Capacitance	C_{iss}	See Specified Test circuit		45		pF
Output Capacitance	C_{oss}			20		
Reverse Transfer Capacitance	C_{rss}			5		
Turn-On Delay Time	$t_{d(on)}$			7		
Turn-On Rise Time	t_r			10		ns
Turn-Off Delay Time	$t_{d(off)}$			35		
Turn-Off Fall Time	t_f			20		
Diode Forward Voltage	V_{SD}	$I_S = -0.5A$, $V_{GS} = 0V$		-1		V

■ Marking

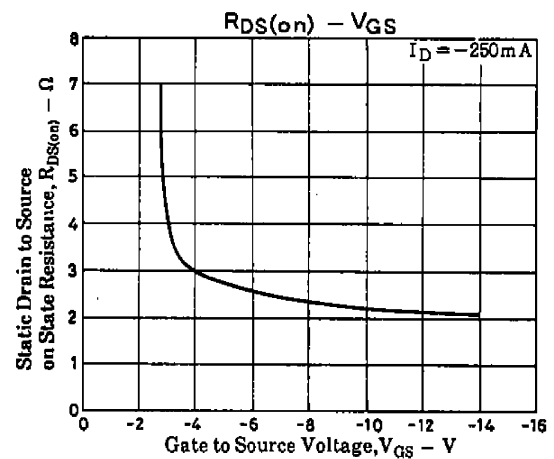
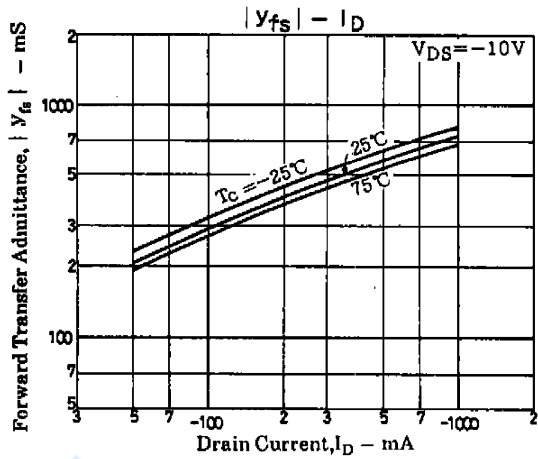
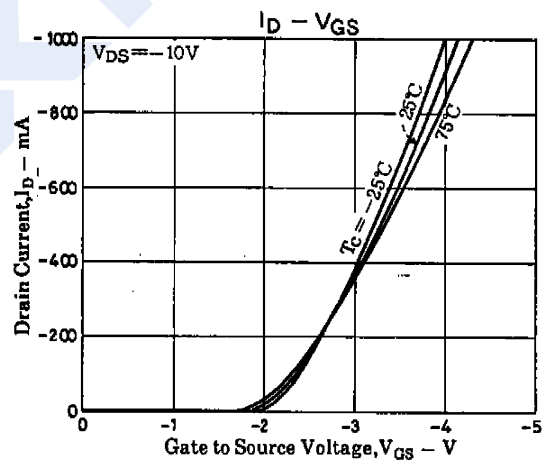
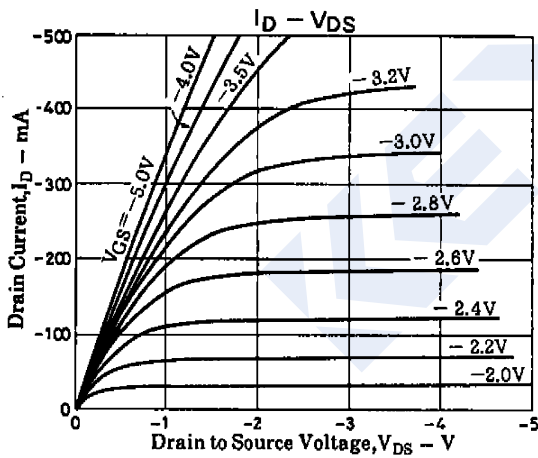
Marking	JE
---------	----

P-Channel MOSFET 2SJ288

Switching Time Test Circuit



■ Typical Characteristics



P-Channel MOSFET 2SJ288

■ Typical Characteristics

